

Vishay Semiconductors

HALOGEN FREE

Infrared Emitting Diode, 875 nm, GaAlAs



DESCRIPTION

The TSHA520. series are infrared, 875 nm emitting diodes in GaAlAs technology, molded in a clear, untinted plastic package.

FEATURES

Package type: leaded
Package form: T-1¾
Dimensions (in mm): Ø 5
Leads with stand-off

• Peak wavelength: $\lambda_p = 875 \text{ nm}$

· High reliability

• Angle of half intensity: $\varphi = \pm 12^{\circ}$

· Low forward voltage

• Suitable for high pulse current operation

 Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

• Halogen-free according to IEC 61249-2-21 definition

APPLICATIONS

- Infrared remote control and free air data transmission systems
- This emitter series is dedicated to systems with panes in transmission space between emitter and detector, because of the low absorbtion of 875 nm radiation in glass

| PRODUCT SUMMARY | | | | | |
|-----------------|------------------------|---------|---------------------|---------------------|--|
| COMPONENT | I _e (mW/sr) | φ (deg) | λ _P (nm) | t _r (ns) | |
| TSHA5200 | 40 | ± 12 | 875 | 600 | |
| TSHA5201 | 50 | ± 12 | 875 | 600 | |
| TSHA5202 | 60 | ± 12 | 875 | 600 | |
| TSHA5203 | 65 | ± 12 | 875 | 600 | |

Note

Test conditions see table "Basic Characteristics"

| ORDERING INFORMATION | | | | | | |
|----------------------|-----------|------------------------------|--------------|--|--|--|
| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM | | | |
| TSHA5200 | Bulk | MOQ: 4000 pcs, 4000 pcs/bulk | T-1¾ | | | |
| TSHA5201 | Bulk | MOQ: 4000 pcs, 4000 pcs/bulk | T-1¾ | | | |
| TSHA5202 | Bulk | MOQ: 4000 pcs, 4000 pcs/bulk | T-1¾ | | | |
| TSHA5203 | Bulk | MOQ: 4000 pcs, 4000 pcs/bulk | T-1¾ | | | |

Note

MOQ: minimum order quantity

| ABSOLUTE MAXIMUM RATINGS | | | | | | |
|-------------------------------------|--|-------------------|---------------|------|--|--|
| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT | | |
| Reverse voltage | | V _R | 5 | V | | |
| Forward current | | I _F | 100 | mA | | |
| Peak forward current | $t_p/T = 0.5, t_p = 100 \mu s$ | I _{FM} | 200 | mA | | |
| Surge forward current | t _p = 100 μs | I _{FSM} | 2.5 | Α | | |
| Power dissipation | | P _V | 180 | mW | | |
| Junction temperature | | Tj | 100 | °C | | |
| Operating temperature range | | T _{amb} | - 40 to + 85 | °C | | |
| Storage temperature range | | T _{stg} | - 40 to + 100 | °C | | |
| Soldering temperature | $t \le 5$ s, 2 mm from case | T _{sd} | 260 | °C | | |
| Thermal resistance junction/ambient | J-STD-051, leads 7 mm, soldered on PCB | R _{thJA} | 230 | K/W | | |

Note

 T_{amb} = 25 °C, unless otherwise specified

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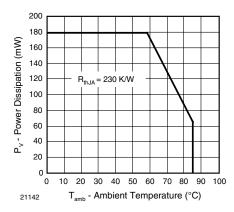


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

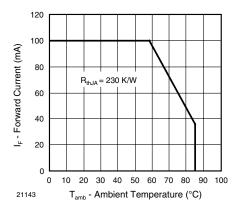


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS | | | | | | | |
|---|---|------------------|---------------------|-------|------|------|--|
| PARAMETER | TEST CONDITION | SYMBOL | IBOL MIN. TYP. MAX. | | MAX. | UNIT | |
| Forward voltage | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | V _F | | 1.5 | 1.8 | V | |
| Temperature coefficient of V _F | I _F = 100 mA | TK _{VF} | | - 1.6 | | mV/K | |
| Reverse current | V _R = 5 V | I _R | | | 100 | μΑ | |
| Junction capacitance | $V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0$ | C _j | | 20 | | pF | |
| Temperature coefficient of φ _e | I _F = 20 mA | TKφ _e | | - 0.7 | | %/K | |
| Angle of half intensity | | φ | | ± 12 | | deg | |
| Peak wavelength | I _F = 100 mA | λ_{p} | | 875 | | nm | |
| Spectral bandwidth | I _F = 100 mA | Δλ | | 80 | | nm | |
| Temperature coefficient of λ_p | I _F = 100 mA | TKλ _p | | 0.2 | | nm/K | |
| Dia a Mara | I _F = 100 mA | t _r | | 600 | | ns | |
| Rise time | I _F = 1 A | t _r | | 300 | | ns | |
| Fall time | I _F = 100 mA | t _f | | 600 | | ns | |
| raii iiiile | I _F = 1 A | t _f | | 300 | | ns | |
| Virtual source diameter | | d | | 3.7 | | mm | |

Note

T_{amb} = 25 °C, unless otherwise specified



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| TYPE DEDICATED CHARACTERISTICS | | | | | | | |
|--------------------------------|---|----------|----------------|------|------|---|-------|
| PARAMETER | TEST CONDITION | PART | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| | 1 1 1 1 1 1 100 | TSHA5200 | V _F | | 2.8 | 3.5 | V |
| Forward valtage | | TSHA5201 | V _F | | 2.8 | 3.5 | V |
| Forward voltage | $I_F = 1 \text{ A}, t_p = 100 \mu s$ | TSHA5202 | V _F | | 2.8 | 3.5 V 3.5 V 3.5 V 3.5 V 3.5 V 125 mW/si 125 mW/si 125 mW/si 125 mW/si 125 mW/si mW/si mW/si mW/si | V |
| | | TSHA5203 | V _F | | 2.8 | | V |
| | | TSHA5200 | I _e | 25 | 40 | 125 | mW/sr |
| | 100 4 | TSHA5201 | I _e | 30 | 50 | 125 | mW/sr |
| | $I_F = 100 \text{ mA}, t_p = 20 \mu \text{s}$ | TSHA5202 | I _e | 36 | 60 | 125 | mW/sr |
| Dedient intensity | | TSHA5203 | I _e | 50 | 65 | 125 | mW/sr |
| Radiant intensity | | TSHA5200 | I _e | 200 | 330 | | mW/sr |
| | I 1 A + 100 ··· | TSHA5201 | I _e | 260 | 400 | | mW/sr |
| | $I_F = 1 \text{ A}, t_p = 100 \mu\text{s}$ | TSHA5202 | I _e | 330 | 460 | | mW/sr |
| | | TSHA5203 | I _e | 400 | 530 | | mW/sr |
| | | TSHA5200 | фe | | 22 | | mW |
| Dadient news | 100 m 4 + 20 | TSHA5201 | фe | | 23 | | mW |
| Radiant power | $I_F = 100 \text{ mA}, t_p = 20 \mu \text{s}$ | TSHA5202 | φ _e | | 24 | | mW |
| | | TSHA5203 | фe | | 25 | | mW |

Note

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BASIC CHARACTERISTICS

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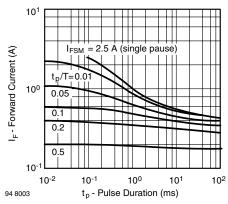


Fig. 3 - Pulse Forward Current vs. Pulse Duration

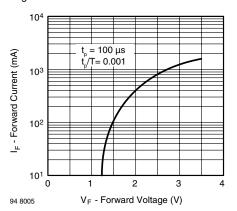


Fig. 4 - Forward Current vs. Forward Voltage

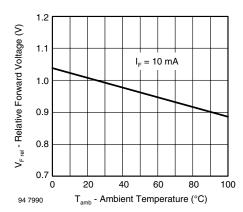


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

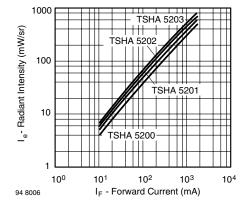


Fig. 6 - Radiant Intensity vs. Forward Current

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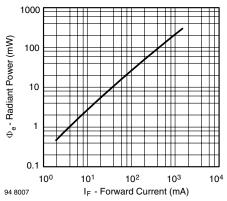


Fig. 7 - Radiant Power vs. Forward Current

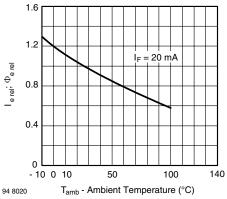


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

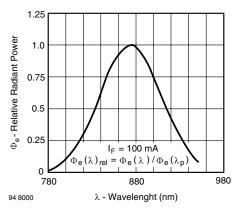


Fig. 9 - Relative Radiant Power vs. Wavelength

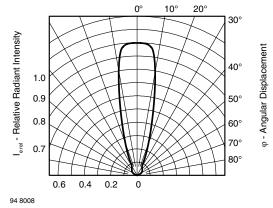
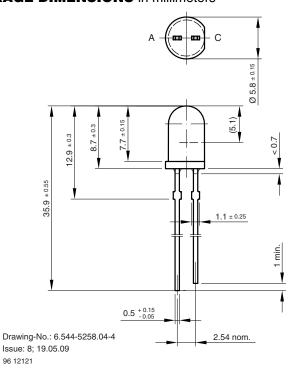
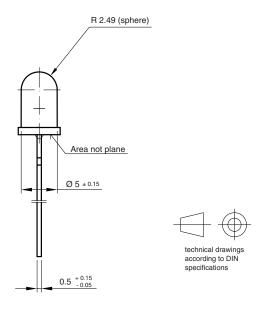


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters









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